

Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameters)
PART NUMBER: 2SK2610
MANUFACTURER: TOSHIBA
Body Diode (Model Parameters) / ESD Protection Diode

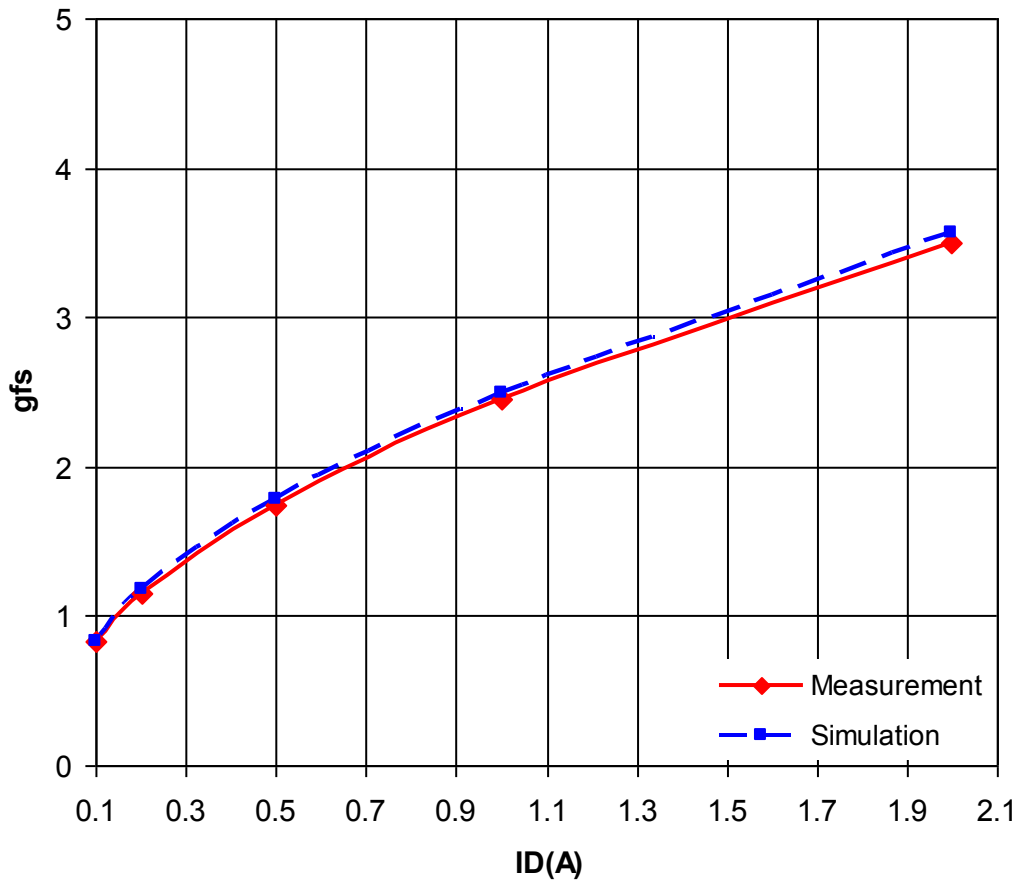


MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

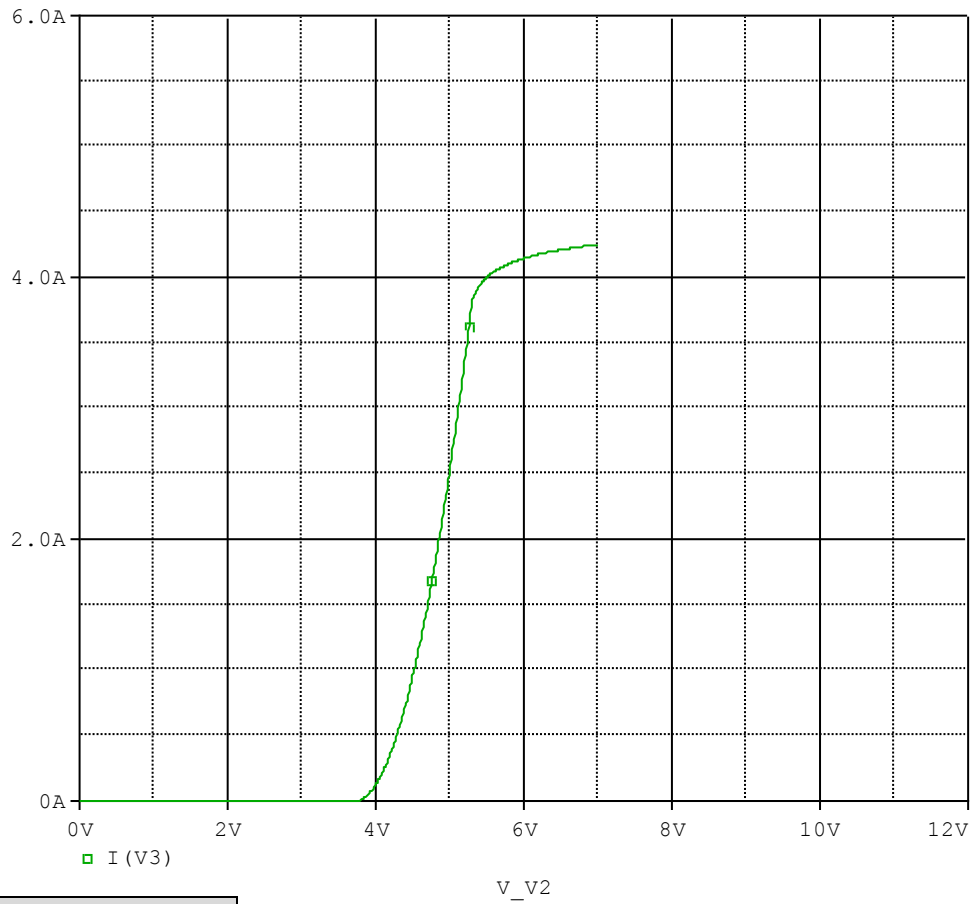


Comparison table

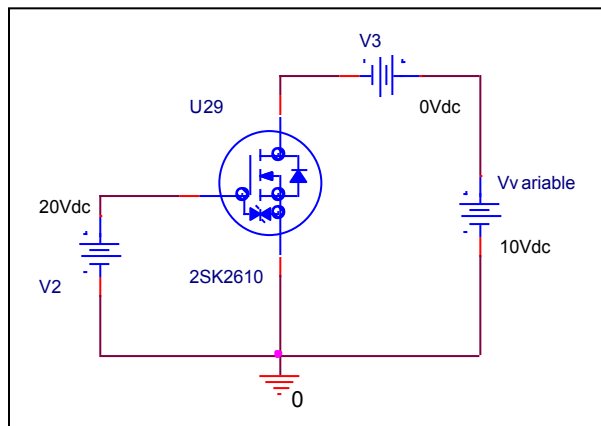
Id(A)	gfs		Error(%)
	Measurement	Simulation	
0.1	0.830	0.833	0.361
0.2	1.150	1.176	2.261
0.5	1.740	1.786	2.644
1	2.450	2.500	2.041
2	3.500	3.571	2.029

Vgs-Id Characteristic

Circuit Simulation result

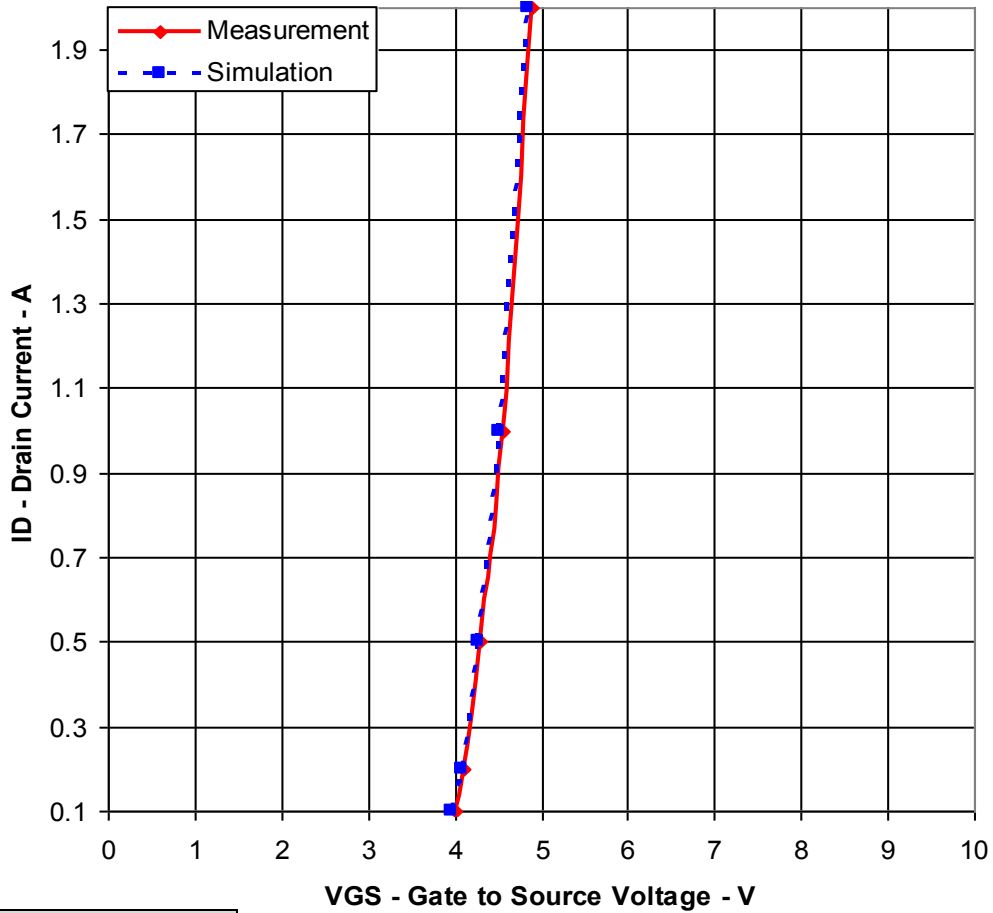


Evaluation circuit



Comparison Graph

Circuit Simulation Result

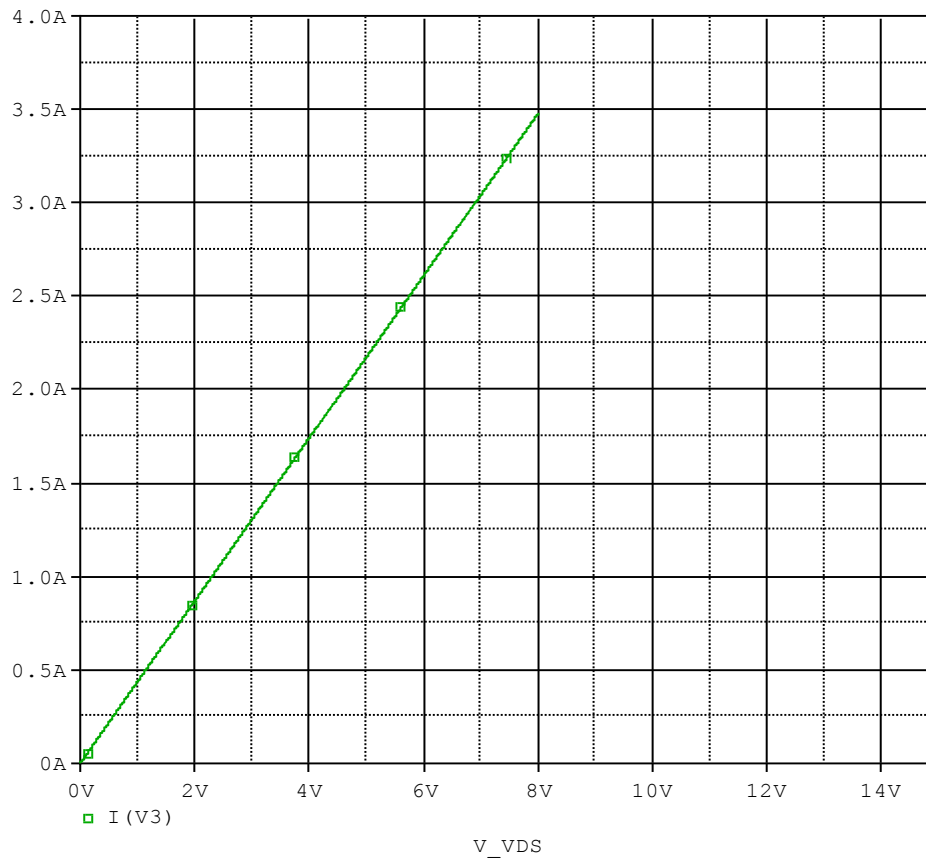


Simulation Result

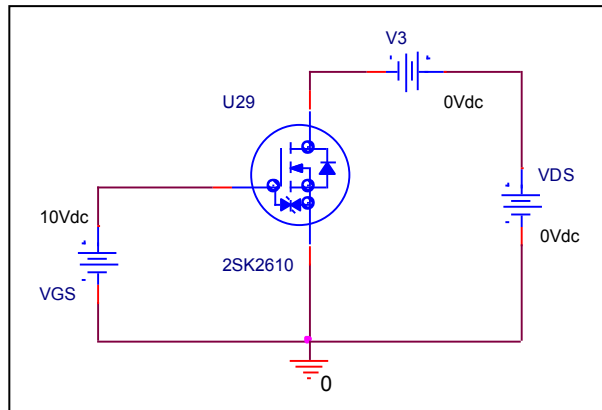
ID(A)	VGS(V)		Error (%)
	Measurement	Simulation	
0.1	4.000	3.971	-0.725
0.2	4.100	4.075	-0.610
0.5	4.300	4.282	-0.419
1	4.550	4.518	-0.703
2	4.900	4.855	-0.918

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

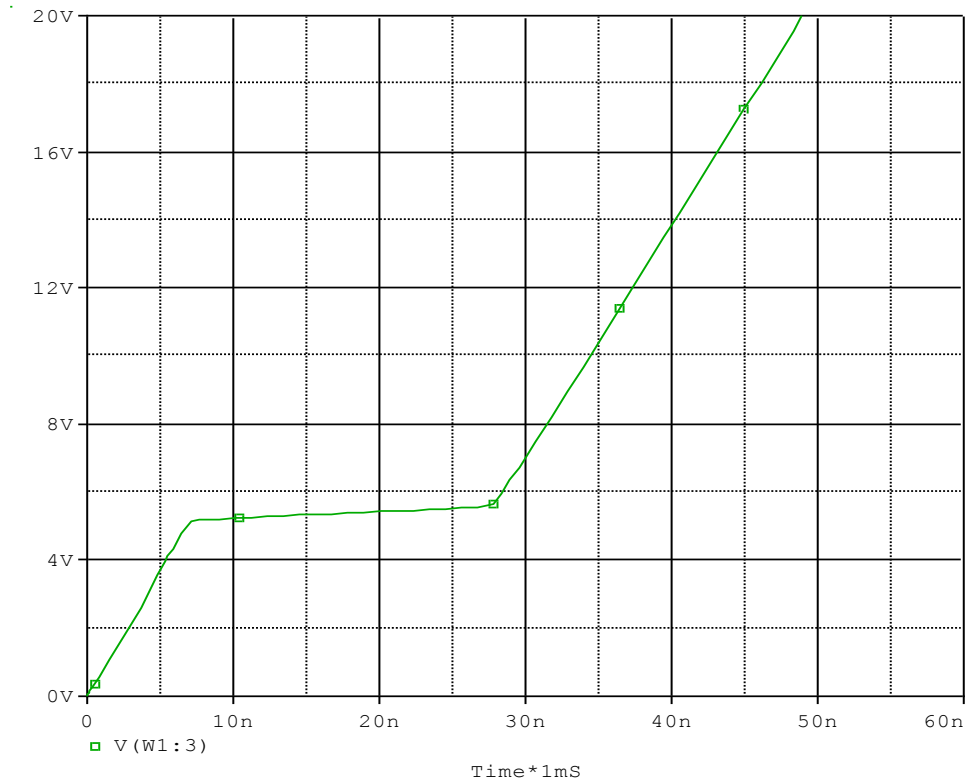


Simulation Result

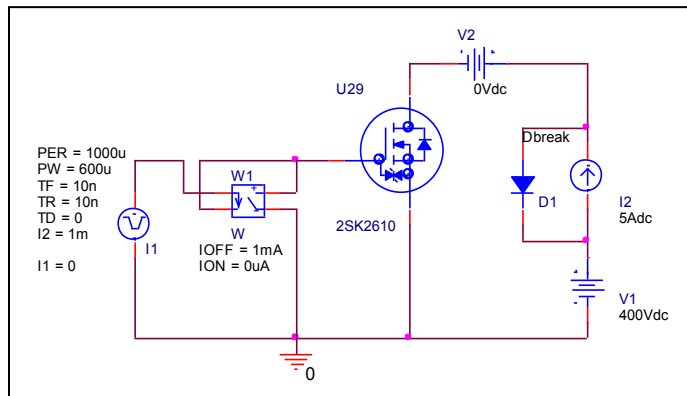
I_D=3A, V_{GS}=10V	Measurement		Simulation		Error (%)
R_{DS} (on)	2.300	Ω	2.300	Ω	0

Gate Charge Characteristic

Circuit Simulation result



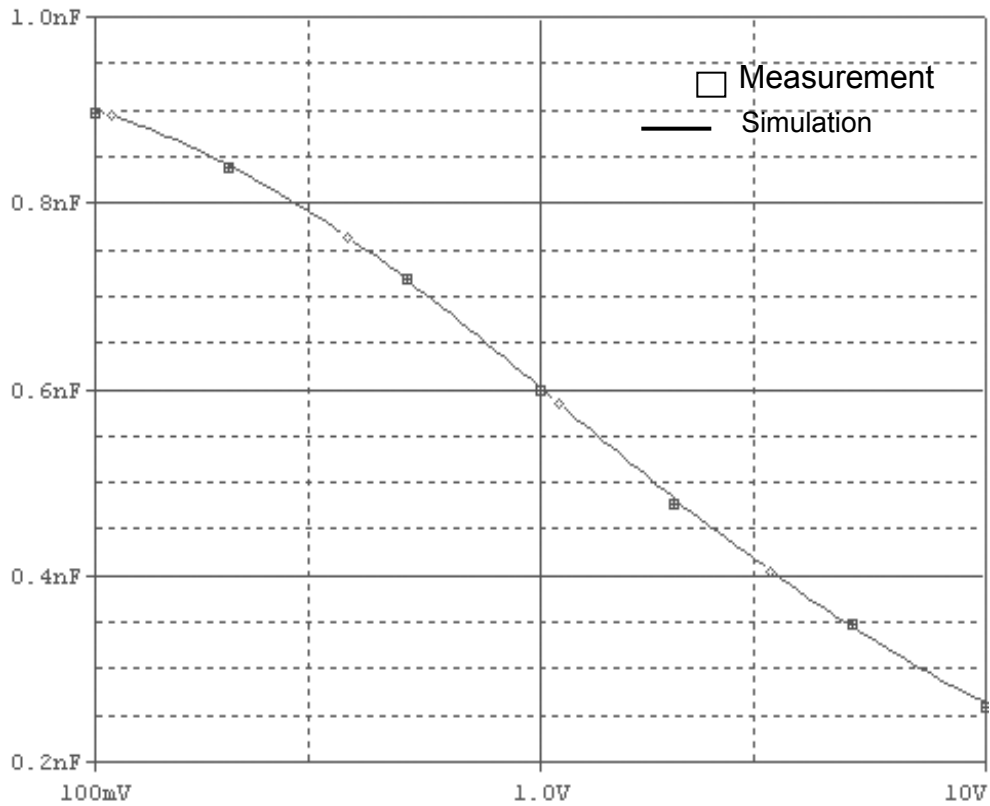
Evaluation circuit



Simulation Result

$V_{DD}=400V, I_D=5A$ $, V_{GS}=10V$	Measurement	Simulation	Error (%)
Qgs(nC)	7.000	7.066	0.943
Qgd(nC)	20.000	20.081	0.405
Qg	42.000	34.502	-17.852

Capacitance Characteristic

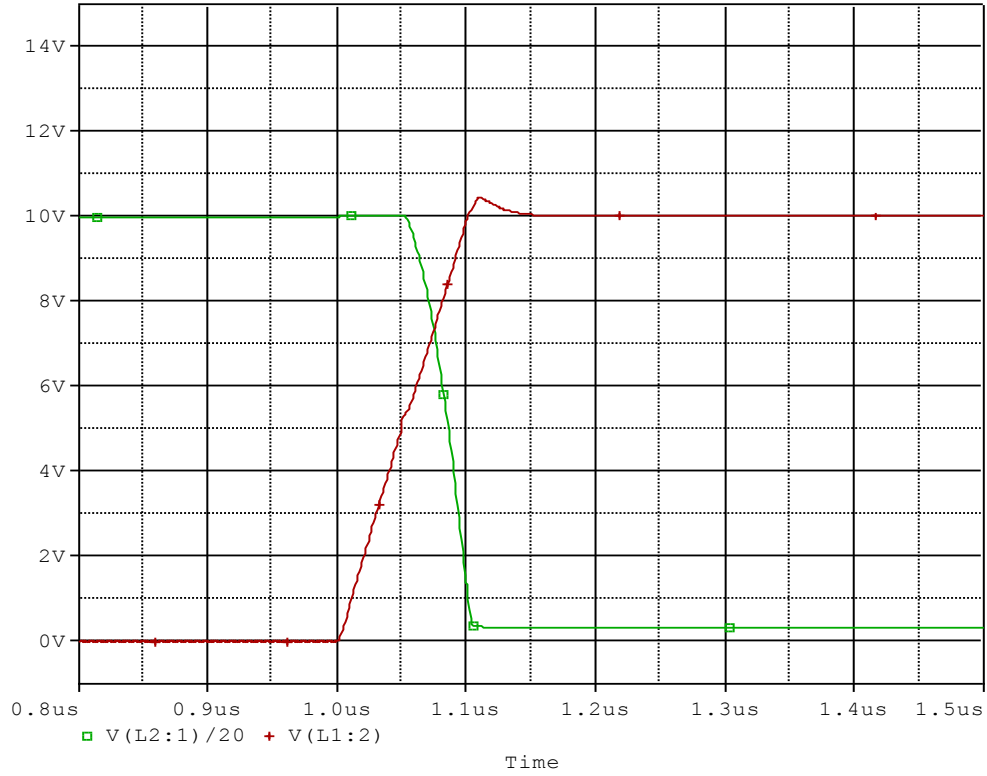


Simulation Result

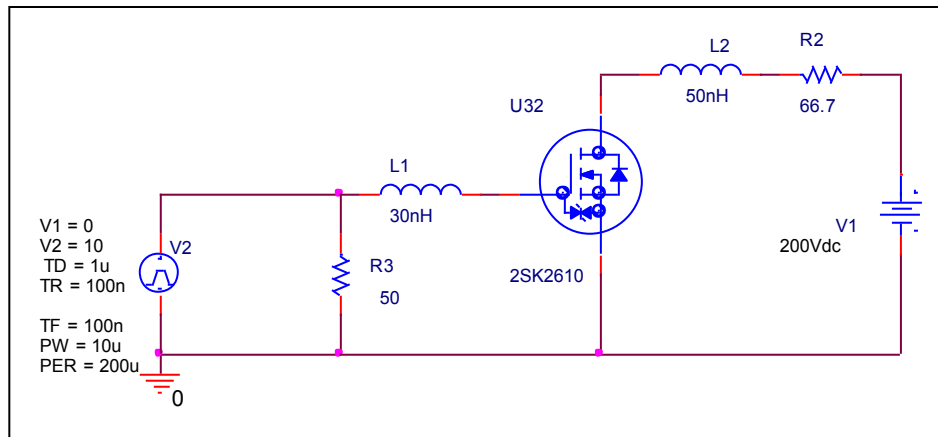
V _{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.1	900	904	0.444
0.2	840	842	0.238
0.5	720	721	0.139
1	600	601	0.167
2	480	483	0.625
5	350	350	0.000
10	260	261	0.385

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

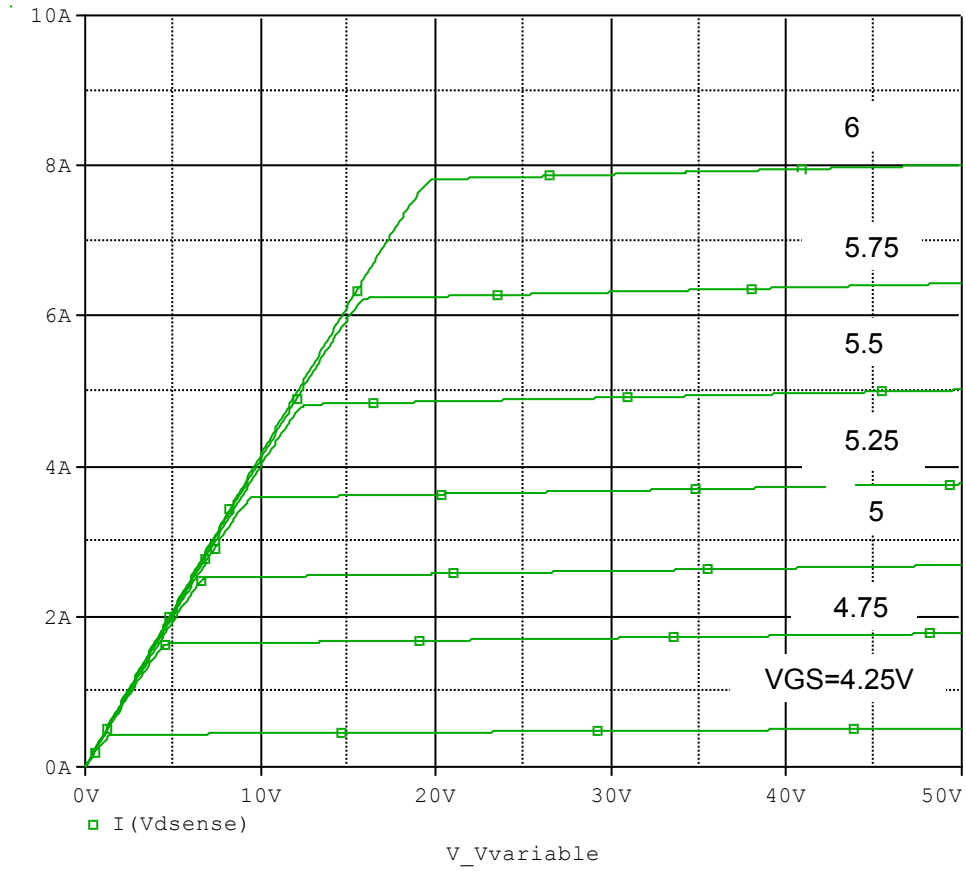


Simulation Result

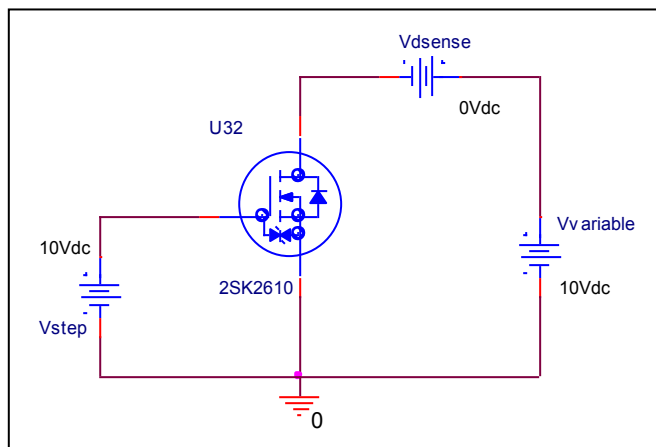
$I_D=3A, V_{DD}=200V$ $V_{GS}=0/10V$	Measurement	Simulation	Error(%)
Ton(ns)	90.000	90.462	0.513

Output Characteristic

Circuit Simulation result

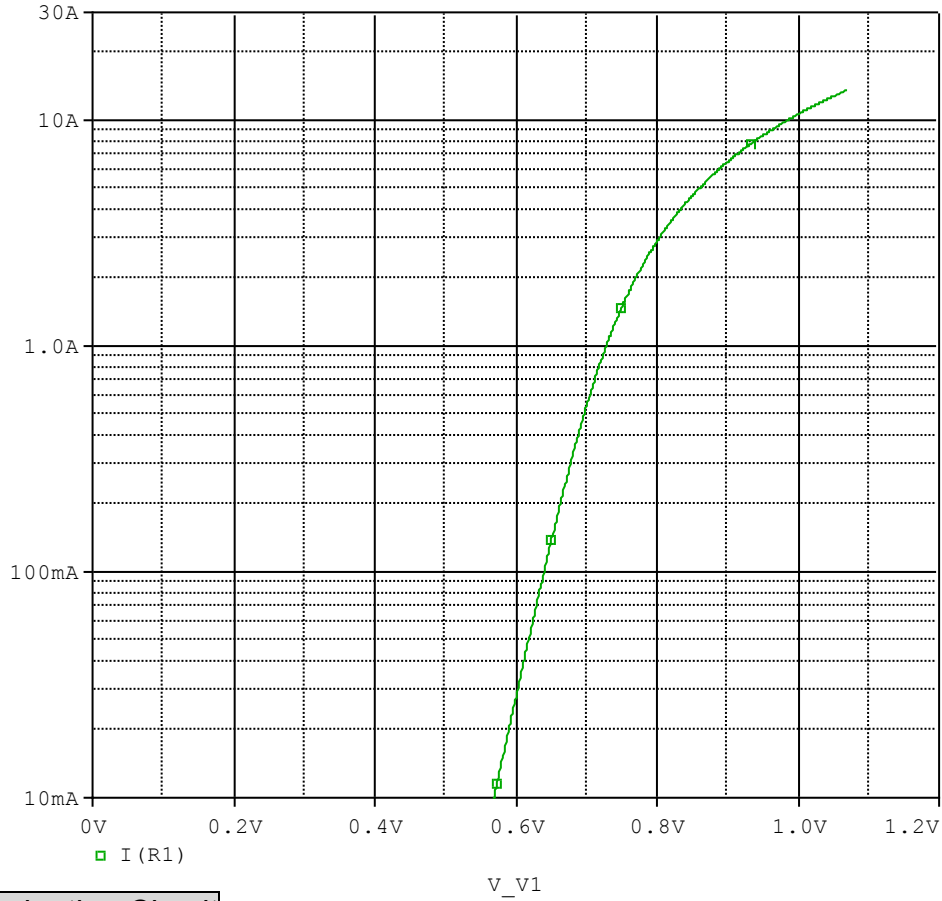


Evaluation circuit

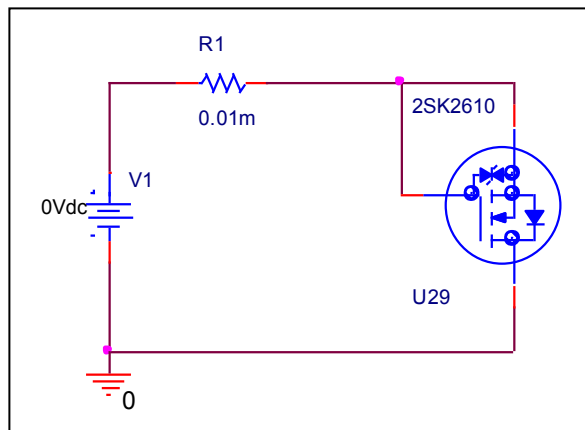


BODY DIODE Forward Current Characteristic

Circuit Simulation Result

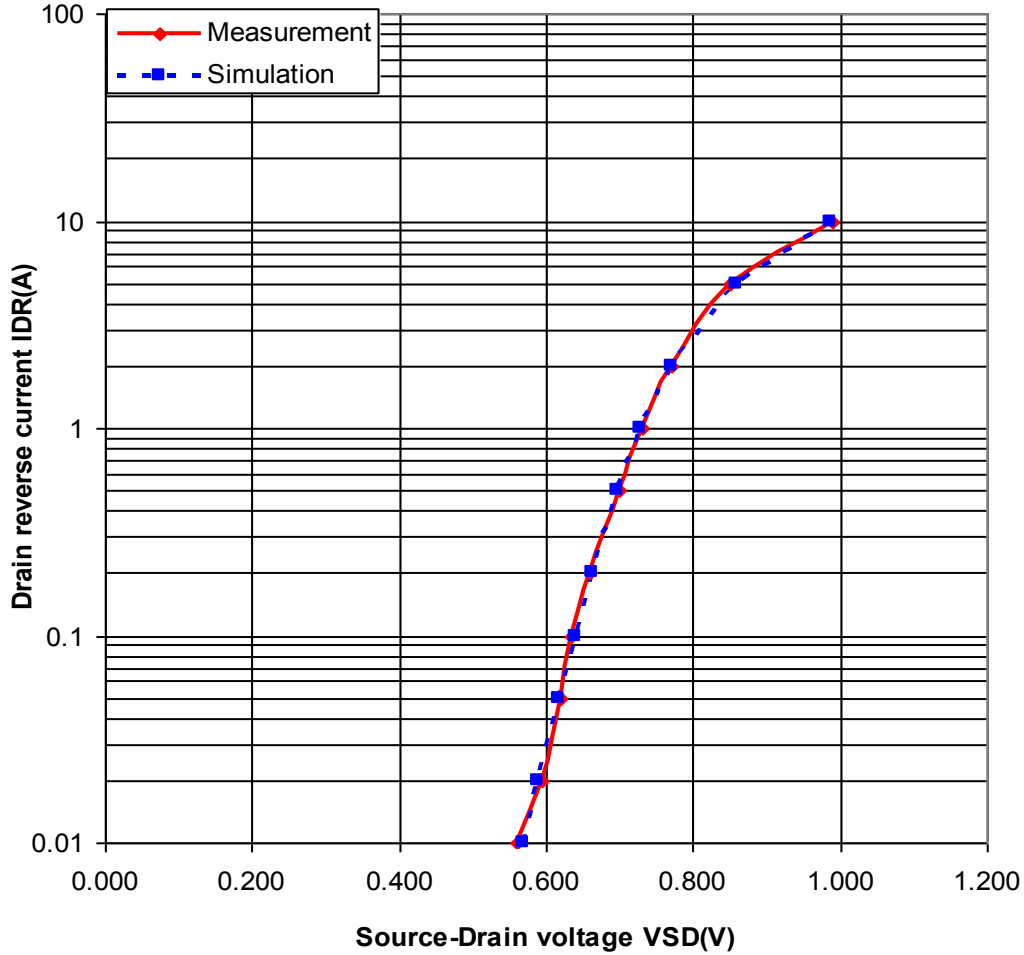


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

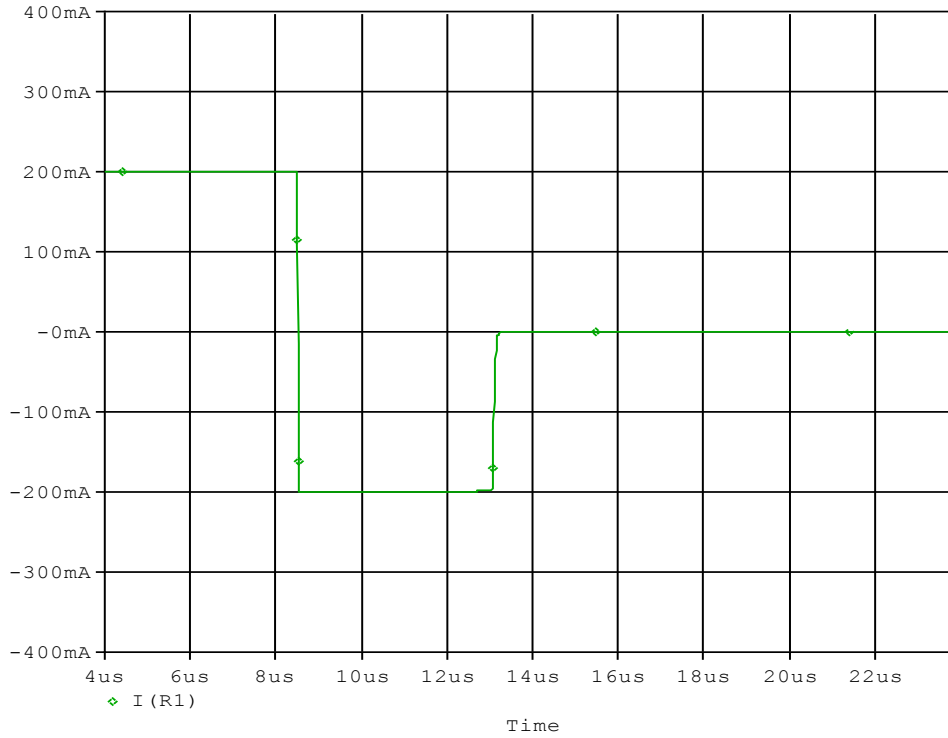


Simulation Result

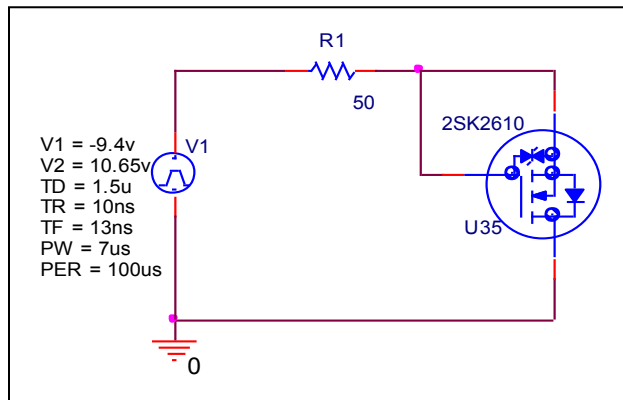
IDR(A)	VSD(V)		%Error
	Measuremen	Simulation	
0.01	0.560	0.568	1.429
0.02	0.595	0.590	-0.840
0.05	0.620	0.618	-0.323
0.1	0.635	0.639	0.630
0.2	0.660	0.662	0.303
0.5	0.700	0.697	-0.429
1	0.730	0.728	-0.274
2	0.770	0.770	0.000
5	0.850	0.860	1.176

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

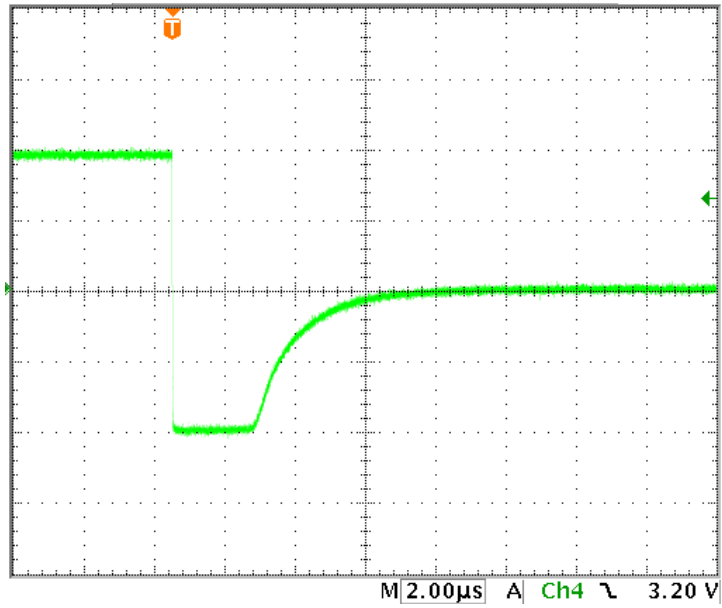


Compare Measurement vs. Simulation

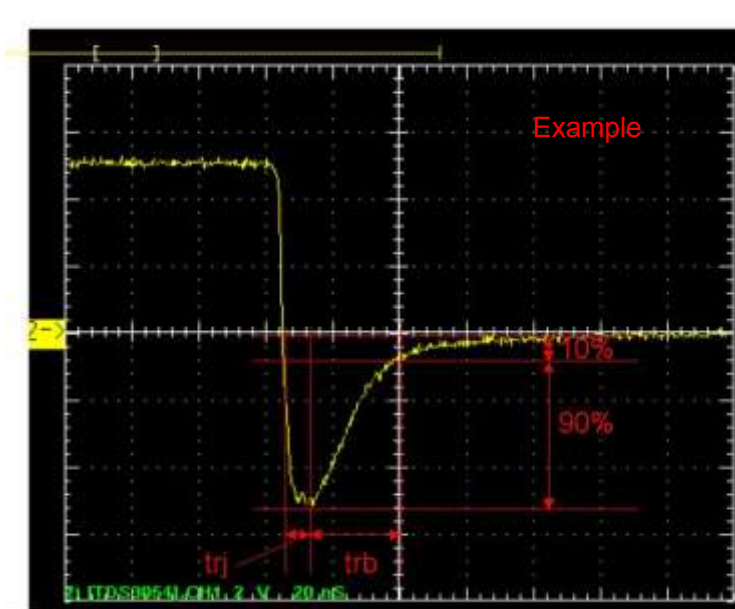
Trr	Measurement	Simulation	Error (%)
Trj+Trb(us)	4.620	4.635	0.325

Reverse Recovery Characteristic

Reference



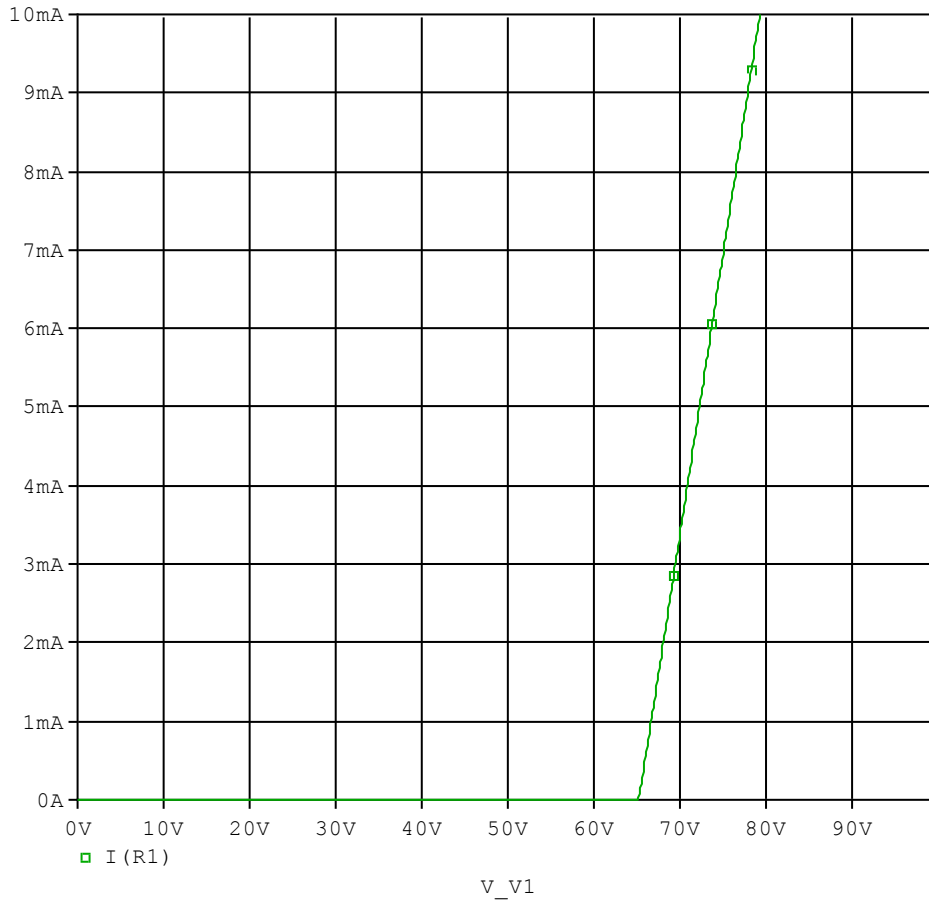
Trj=2.340 (us)
Trb=2.280(us)
Conditions: Ifwd=Irev=0.2(A), RI=50



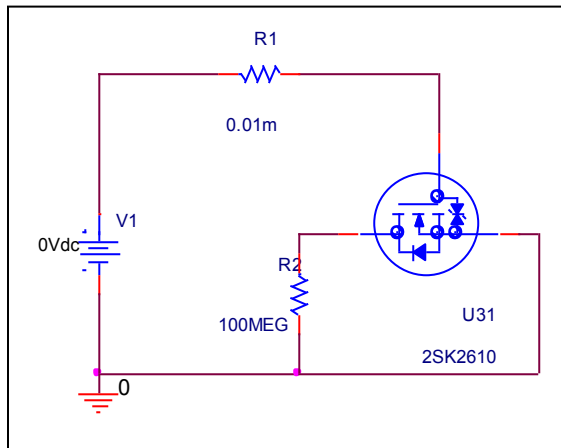
Relation between trj and trb

ESD PROTECTION DIODE Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic

Reference

